

RETC Project Report: C-CS-2306-LRI-294

RETC

PVsyst V7.4.8

	PV module - I	_R5-72HBD-540M ————	
Manufacturer	LONGi	Commercial data	
Model	LR5-72HBD-540M	Data source : RETCCT-LRI29	4e-240920
Pnom STC power (manufacturer)	540 Wp	Technology	Si-mono
Module size (W x L)	1.134 x 2.278 m ²	Rough module area (Amodule)	2.58 m²
lumber of cells	2 x 72	Sensitive area (cells) (Acells)	2.41 m²
pecifications for the model (manufacturer or measureme	ent data)	
Reference temperature (TRef)	25 °C	Reference irradiance (GRef)	1000 W/m ²
Open circuit voltage (Voc)	49.5 V	Short-circuit current (Isc)	13.85 A
lax. power point voltage (Vmpp)	41.7 V	Max. power point current (Impp)	12.97 A
> maximum power (Pmpp)	540.2 W	Isc temperature coefficient (mulsc)	4.3 mA/°C
One-diode model parameters			
Shunt resistance (Rshunt)	450 Ω	Diode saturation current (IoRef)	0.015 nA
Serie resistance (Rserie)	0.21 Ω	Voc temp. coefficient (MuVoc)	-134 mV/°C
pecified Pmax temper. coeff. (muF		Diode quality factor (Gamma)	0.97
	,	Diode factor temper. coeff. (muGamma)	0.000 1/°C
Reverse Bias Parameters. for	use in behaviour of PV array	ys under partial shadings or mismatch	
Reverse characteristics (dark) (BRe		(quadratic factor (per cell))	
lumber of by-pass diodes per mod		Direct voltage of by-pass diodes	-0.7 V
Model results for standard co	nditions (STC: T=25 °C G=	:1000 W/m². AM=1.5)	
Max. power point voltage (Vmpp)	41.1 V	Max. power point current (Impp)	13.18 A
aximum power (Pmpp)	541.1 Wp	Power temper. coefficient (muPmpp)	-0.34 %/°C
ifficiency(/ Module area) (Eff_mod)	•	Fill factor (FF)	0.789
Efficiency(/ Cells area) (Eff_cells)	22.4 %	,	
40			
16 Cells temp. = 25 °		Gi, LR5-72HBD-540M	'
- Odis temp 20			-
14	Incident Irrad. = 1000 W/m²	541.1 W	_
		JH1.1 VV]
			1
12 —		\	-
	Incident Irrad. = 800 W/m²	433.8 V	
10 —		\ \	-
L		\ \]
<u> </u>	Incident Irrad. = 600 W/m²	325.0 W	
Current [A]		<u>a</u>	-
C		\ \	
ĺ		\	1
_1	Incident Irrad. = 400 W/m ²	215.2 W	-
6 –			
6		~ \	
6 -			
4 –			-

0

10

20

Voltagge [V]

40

50